F.E. (Semester – II) (RC 2016-17) Examination, Nov./Dec. 2018 **FUNDAMENTALS OF ELECTRONICS AND** TELECOMMUNICATION ENGINEERING

Total Marks: 100 **Duration: 3 Hours**

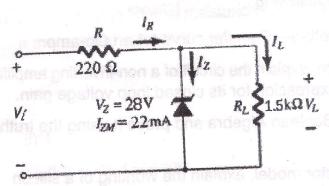
Instructions:

- 1) Answer five questions. At least two from Part A, two from Part - B, and one from Part - C.
- 2) Assume suitable data if necessary.
- 3) Figures to the right indicate full marks.

PART - A

Answer any two questions from the following:

- 1. a) With the help of neat sketch explain forward biasing of PN junction diode. 5 b) Draw the V/I characteristics of a Silicon Diode and explain the term 5
 - Threshold voltage.
 - 5 c) Differentiate between Avalanche and Zener breakdown.
 - d) Over what range of input voltages will the Zener diode circuit shown in figure below maintain 28 V across a 1.5 K load, assuming that series resistance $R = 200 \Omega$ and Zener current rating is 22 mA?



- 2. a) Derive the relationship between αdc and βdc .
 - b) With the help of a neat circuit diagram explain the output characteristics of a npn BJT connected in CB configuration.
 - c) With respect to biasing circuits of a Bipolar junction transistor, explain the concept of thermal runaway.

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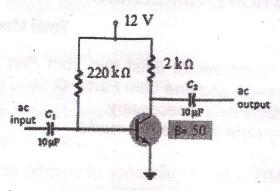
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d) For the fixed bias network shown below, determine the following :

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- a) I_{BC}
- b) Ico
- c) V_{CEQ}
- d) V_{BC}
- e) 1 ...



3. a) Derive an expression for the rectification efficiency of a half wave rectifier.

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b) Explain the construction and working of a light emitting diode.

c) With the help of a neat diagram explain the construction of N-channel JFET.

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d) What are the various ways in which transfer characteristics of a JFET can be plotted?

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PART - B

Answer any two questions from the following:

4. a) Draw and explain the ideal voltage. Transfer curve for an Op-amp.

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b) With the help of a neat diagram, explain the circuit of a non-inverting amplifier using op-amp and give the expression for its closed loop voltage gain.

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c) State the associative law in Boolean Algebra and prove it using the truth table method.

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d) With the help of a two-transistor model, explain the working of a silicon controlled rectifier.

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5. a) With the help of neat diagrams, explain the construction, working and characteristics of a thermistor.

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b) With the help of neat sketches explain the construction, working and characteristics of LVDT.

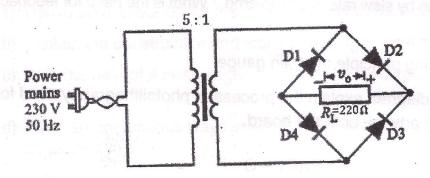
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- 8. a) In the bridge type circuit shown in figure below, the diodes are assumed to be ideal. Find:
 - i) the d.c. output voltage
 - ii) the peak inverse voltage
 - iii) the output frequency
 - iv) ripple factor.

Assume primary to secondary turns ratio to be 5:1.



- b) Differentiate between Emitter, Base and Collector.
- c) With the help of logic diagrams, explain why NAND gate is called a universal gate.
- d) Explain the following steps involved in the manufacturing of a single-sided printed circuit board :
 - i) Etching

ii) Coating.